

2N3903, 2N3904

General Purpose Transistors

NPN Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	40	Vdc
Collector - Base Voltage	V_{CBO}	60	Vdc
Emitter - Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

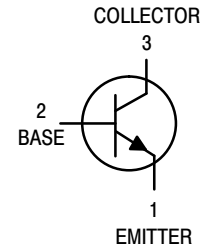
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates Data in addition to JEDEC Requirements.

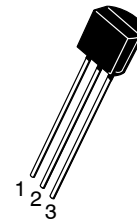


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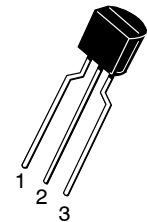
<http://onsemi.com>



TO-92
CASE 29
STYLE 1

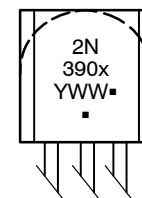


STRAIGHT LEAD
BULK PACK



BENT LEAD
TAPE & REEL
AMMO PACK

MARKING DIAGRAMS



- x = 3 or 4
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 2) ($I_C = 1.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	60	–	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{EB} = 3.0\text{ Vdc}$)	I_{BL}	–	50	nAdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{EB} = 3.0\text{ Vdc}$)	I_{CEX}	–	50	nAdc

ON CHARACTERISTICS

DC Current Gain (Note 2) ($I_C = 0.1\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 50\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$)	2N3903	h_{FE}	20	–	–
	2N3904		40	–	–
	2N3903		35	–	–
	2N3904		70	–	–
	2N3903		50	150	–
	2N3904		100	300	–
	2N3903		30	–	–
	2N3904		60	–	–
Collector – Emitter Saturation Voltage (Note 2) ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$) ($I_C = 50\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$)		$V_{CE(sat)}$	–	0.2	Vdc
			–	0.3	
Base – Emitter Saturation Voltage (Note 2) ($I_C = 10\text{ mAdc}$, $I_B = 1.0\text{ mAdc}$) ($I_C = 50\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$)		$V_{BE(sat)}$	0.65	0.85	Vdc
			–	0.95	

SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	2N3903	f_T	250	–	MHz
	2N3904		300	–	
Output Capacitance ($V_{CB} = 5.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)		C_{obo}	–	4.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)		C_{ibo}	–	8.0	pF
Input Impedance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	2N3903	h_{ie}	1.0	8.0	$k\ \Omega$
	2N3904		1.0	10	
Voltage Feedback Ratio ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	2N3903	h_{re}	0.1	5.0	$\times 10^{-4}$
	2N3904		0.5	8.0	
Small-Signal Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	2N3903	h_{fe}	50	200	–
	2N3904		100	400	
Output Admittance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)		h_{oe}	1.0	40	μmhos
Noise Figure ($I_C = 100\text{ }\mu\text{Adc}$, $V_{CE} = 5.0\text{ Vdc}$, $R_S = 1.0\text{ k}\ \Omega$, $f = 1.0\text{ kHz}$)	2N3903	NF	–	6.0	dB
	2N3904		–	5.0	

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0\text{ Vdc}$, $V_{BE} = 0.5\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $I_{B1} = 1.0\text{ mAdc}$)		t_d	–	35	ns
Rise Time			t_r	–	35	ns
Storage Time	$(V_{CC} = 3.0\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $I_{B1} = I_{B2} = 1.0\text{ mAdc}$)	2N3903 2N3904	t_s	–	175 200	ns
Fall Time			t_f	–	50	ns

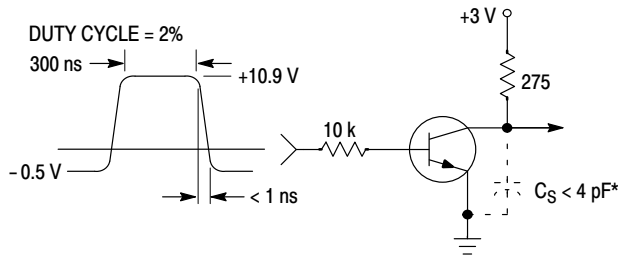
2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$.

2N3903, 2N3904

ORDERING INFORMATION

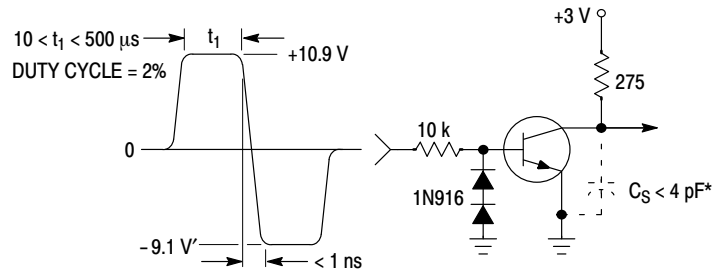
Device	Package	Shipping†
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit



* Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

— $T_J = 25^\circ\text{C}$
 - - - $T_J = 125^\circ\text{C}$

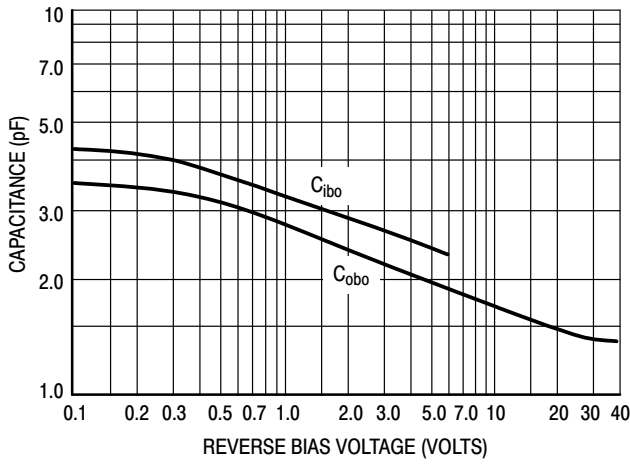


Figure 3. Capacitance

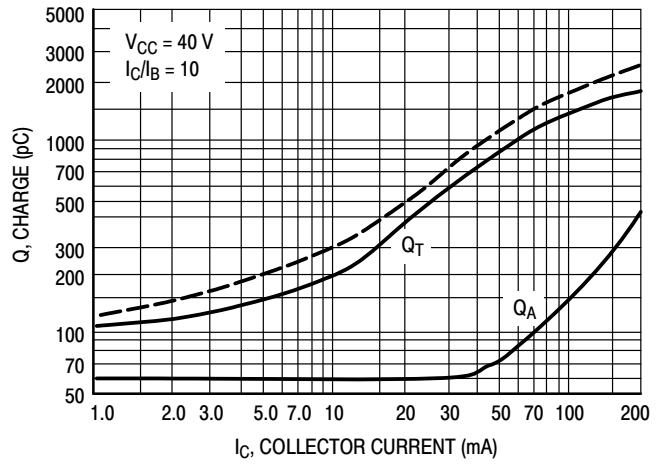


Figure 4. Charge Data

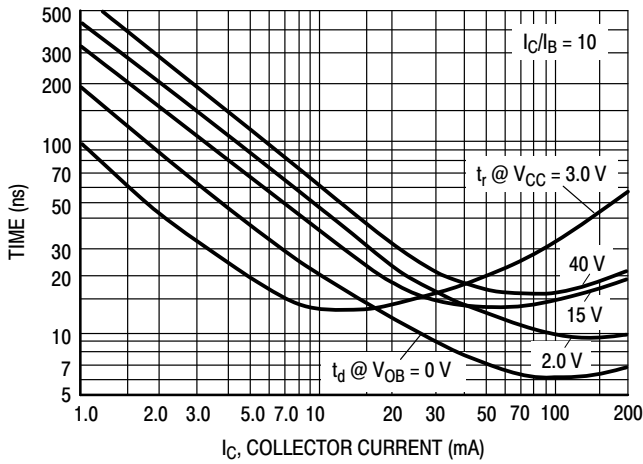


Figure 5. Turn-On Time

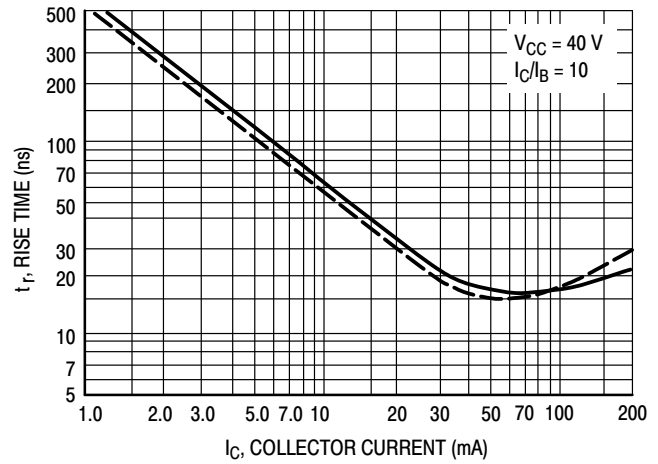


Figure 6. Rise Time

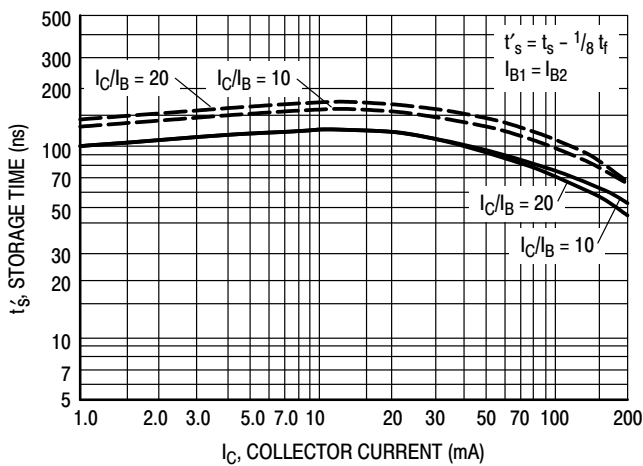


Figure 7. Storage Time

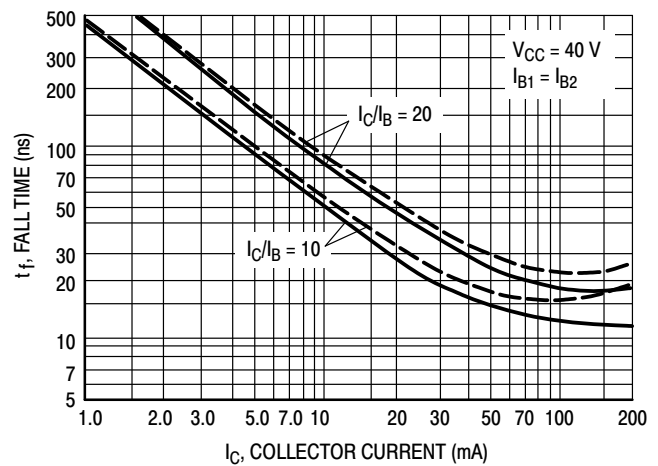


Figure 8. Fall Time

2N3903, 2N3904

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

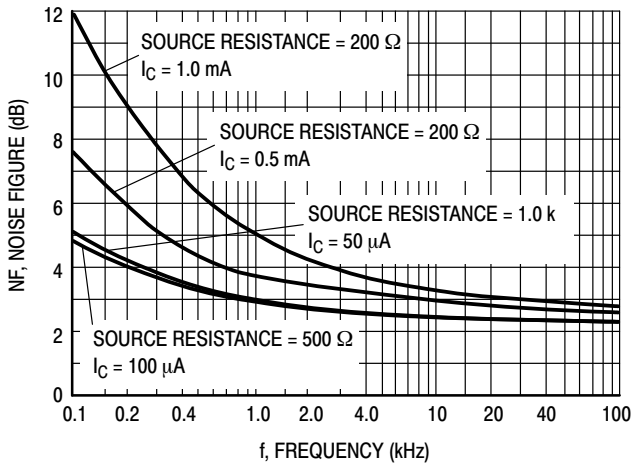


Figure 9.

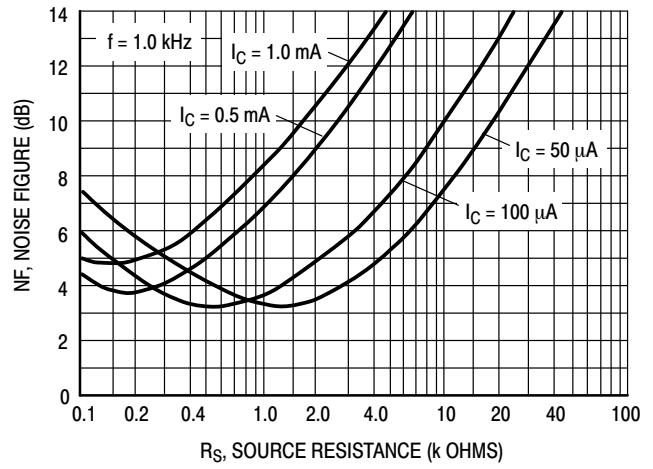


Figure 10.

h PARAMETERS

($V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

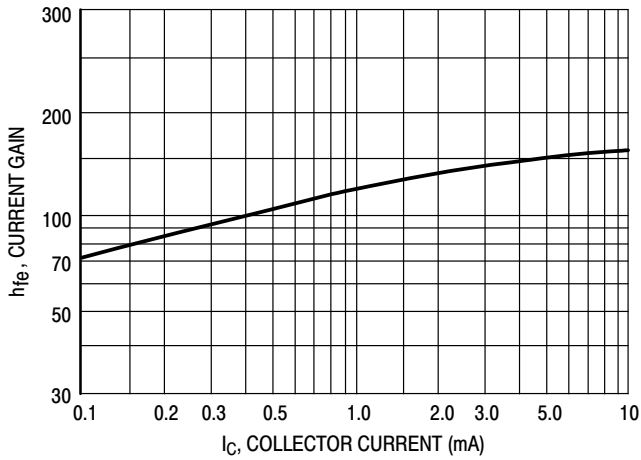


Figure 11. Current Gain

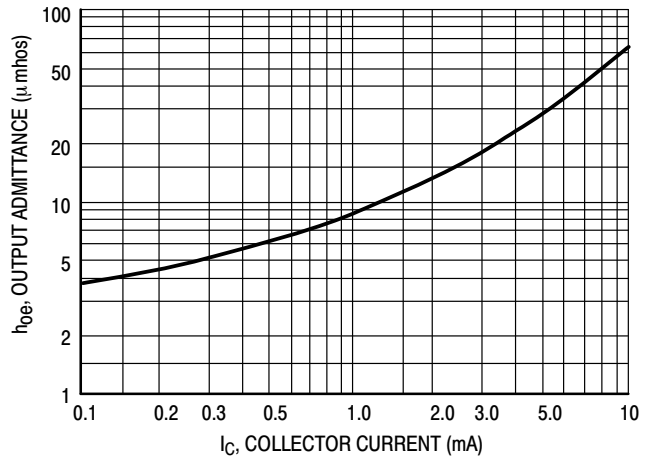


Figure 12. Output Admittance

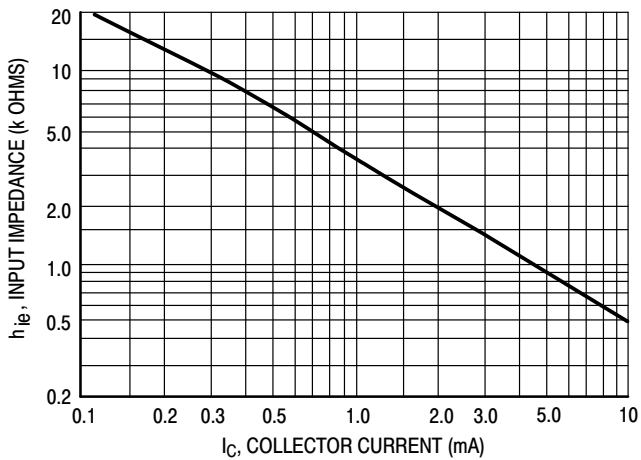


Figure 13. Input Impedance

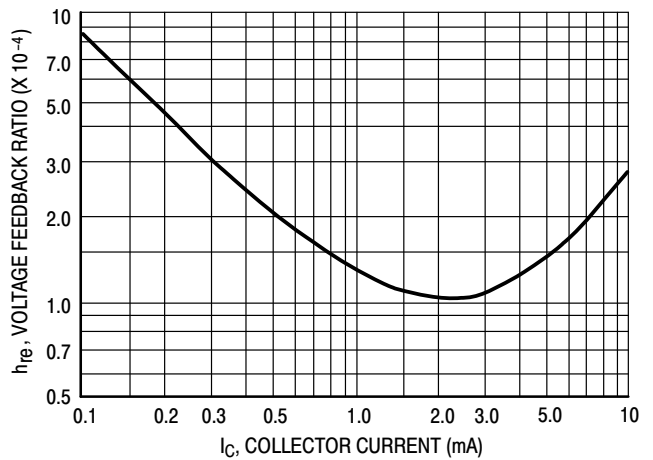


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

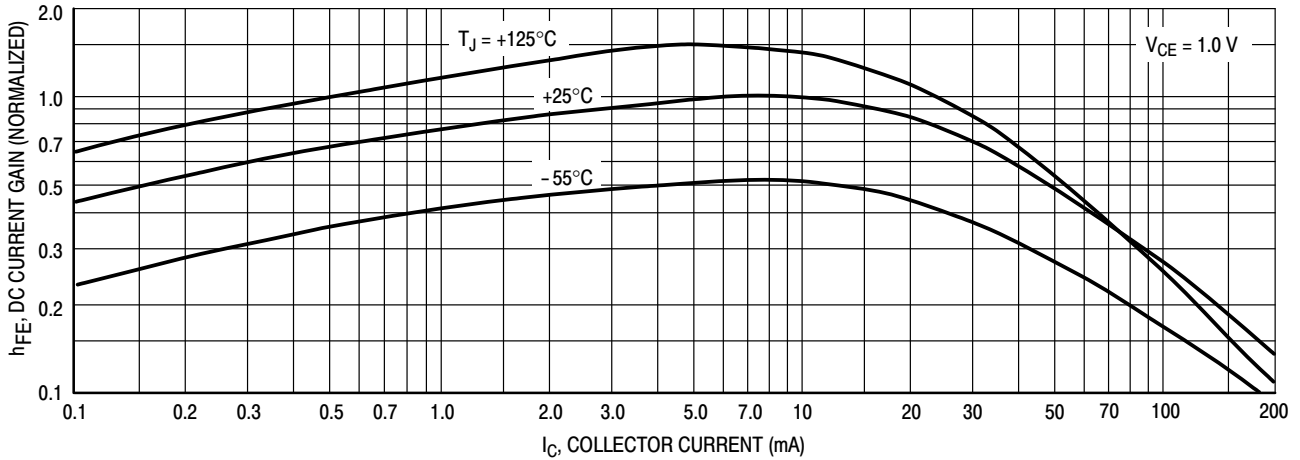


Figure 15. DC Current Gain

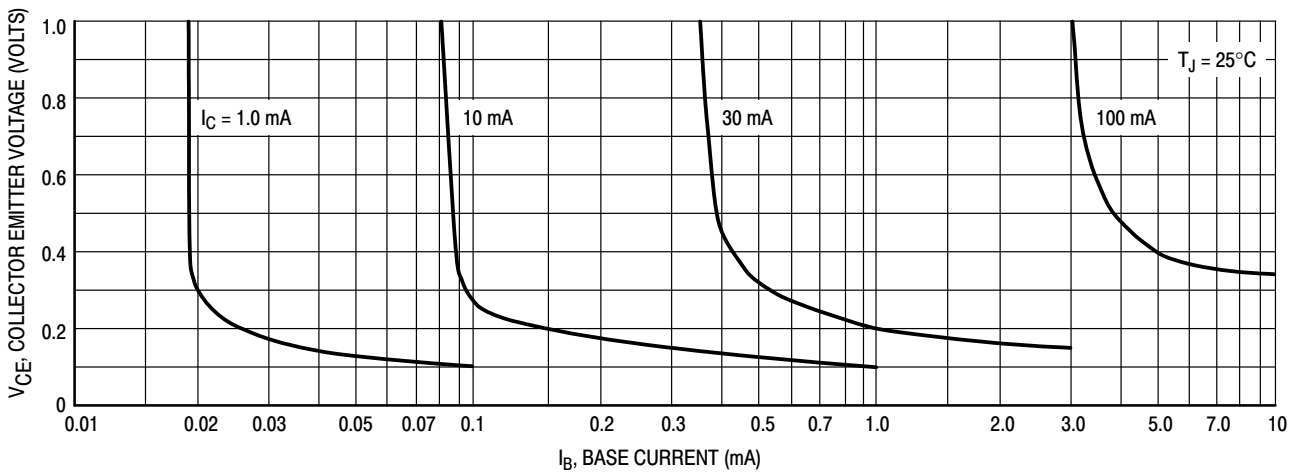


Figure 16. Collector Saturation Region

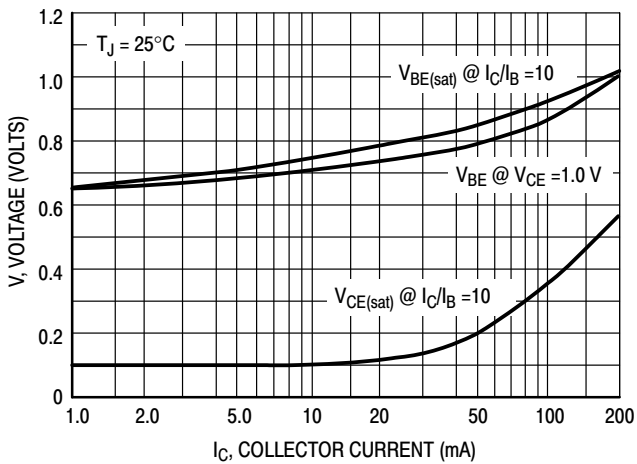


Figure 17. "ON" Voltages

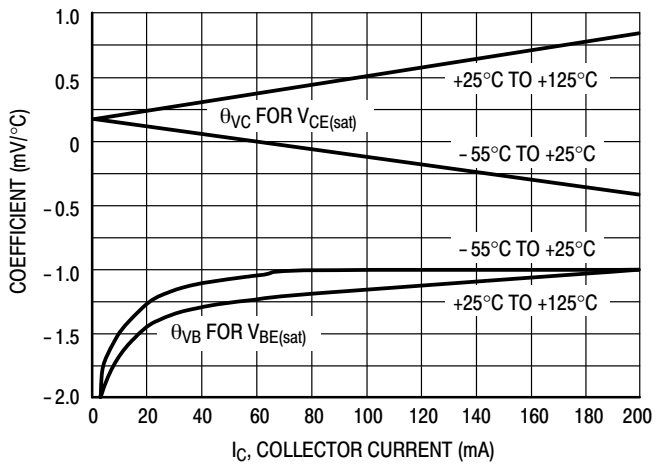


Figure 18. Temperature Coefficients

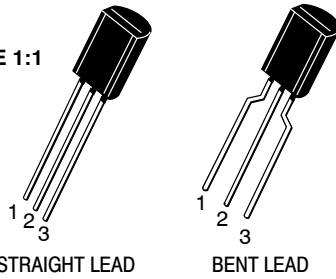
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®

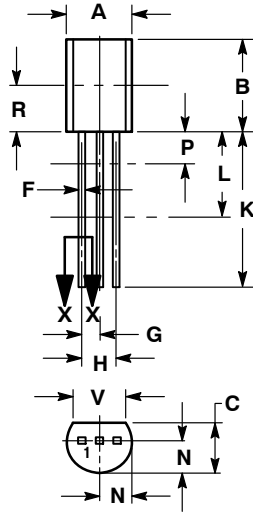


SCALE 1:1



TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE A

DATE 08 MAY 2012

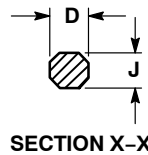


STRAIGHT LEAD

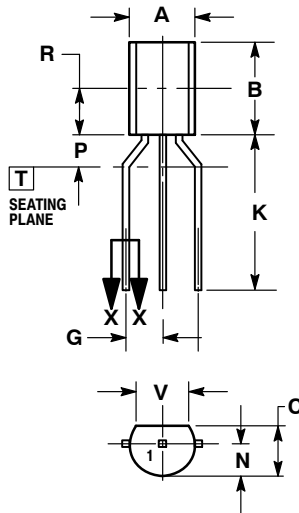
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



SECTION X-X

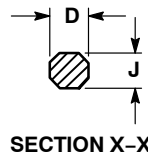


BENT LEAD

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



SECTION X-X

STYLES ON PAGE 2

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**TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE A**

DATE 08 MAY 2012

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 6:
PIN 1. GATE
2. SOURCE & SUBSTRATE
3. DRAIN

STYLE 7:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 8:
PIN 1. DRAIN
2. GATE
3. SOURCE & SUBSTRATE

STYLE 9:
PIN 1. BASE 1
2. EMITTER
3. BASE 2

STYLE 10:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 11:
PIN 1. ANODE
2. CATHODE & ANODE
3. CATHODE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. GATE
3. MAIN TERMINAL 2

STYLE 13:
PIN 1. ANODE 1
2. GATE
3. CATHODE 2

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

STYLE 15:
PIN 1. ANODE 1
2. CATHODE
3. ANODE 2

STYLE 16:
PIN 1. ANODE
2. GATE
3. CATHODE

STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

STYLE 18:
PIN 1. ANODE
2. CATHODE
3. NOT CONNECTED

STYLE 19:
PIN 1. GATE
2. ANODE
3. CATHODE

STYLE 20:
PIN 1. NOT CONNECTED
2. CATHODE
3. ANODE

STYLE 21:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

STYLE 23:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 24:
PIN 1. EMITTER
2. COLLECTOR/ANODE
3. CATHODE

STYLE 25:
PIN 1. MT 1
2. GATE
3. MT 2

STYLE 26:
PIN 1. V_{CC}
2. GROUND 2
3. OUTPUT

STYLE 27:
PIN 1. MT
2. SUBSTRATE
3. MT

STYLE 28:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 29:
PIN 1. NOT CONNECTED
2. ANODE
3. CATHODE

STYLE 30:
PIN 1. DRAIN
2. GATE
3. SOURCE

STYLE 31:
PIN 1. GATE
2. DRAIN
3. SOURCE


STYLE 32:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

STYLE 33:
PIN 1. RETURN
2. INPUT
3. OUTPUT

STYLE 34:
PIN 1. INPUT
2. GROUND
3. LOGIC

STYLE 35:
PIN 1. GATE
2. COLLECTOR
3. EMITTER

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